

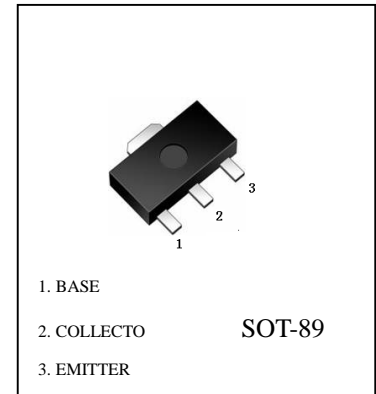
FEATURES

- High DC current gain.
- Low collector-to-emitter saturation voltage.
- Large current capacity.
- Very small size making it easy to provide high-Density, small-sized hybrid IC 'S

Marking: CF

Maximum Ratings (Ta=25 °C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	30	V
Collector-Emitter Voltage	V _{CEO}	25	V
Emitter-Base Voltage	V _{EBO}	15	V
Collector Current -Continuous	I _C	1.2	A
Collector Power dissipation	P _C	0.5	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55to +150	°C

2SC3650 (NPN)


ELECTRICAL CHARACTERISTICS (@ Ta=25 °C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CBO}	I _C =10uA, I _E =0	30			V
Collector-emitter breakdown voltage	V _{CEO}	I _C =1mA, I _B =0	25			V
Emitter-base breakdown voltage	V _{EBO}	I _E =10uA, I _C =0	15			V
Collector cut-off current	I _{CBO}	V _{CB} =20V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =10V, I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =5V, I _C =500mA	800	1500	3200	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =0.5A, I _B =0.01A		0.12	0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =0.5A, I _B =0.01A		0.85	1.2	V
Transition frequency	f _T	V _{CE} =10V, I _C =50mA		220		MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		17		pF

2SC3650 Typical Characteristics

